WHAT IS CLAIMED IS:

- A method comprising:
 forming a magnetic tunnel junction including pinned and sense layers; and
 re-setting a magnetization vector of at least one of the layers.
- 2. The method of claim 1, wherein a magnetization vector is re-set by applying a magnetic field in a direction of interest while annealing the junction.
- 3. The method of claim 1, wherein the pinned layer magnetization vector is re-set by annealing at a temperature above the blocking temperature of the pinned layer while applying a magnetic field in a direction of interest for the pinned layer.
- 4. The method of claim 1, wherein the sense layer magnetization angle is reset by heating the junction above a threshold temperature for easy axis rotation of the sense layer, while applying a magnetic field in a direction of interest for the sense layer.
- 5. The method of claim 1, further comprising testing the switching characteristics of the junction; and re-setting at least one magnetization vector according to test results.
- 6. The method of claim 1, wherein both the sense layer magnetization vector and the pinned layer magnetization vector are re-set by re-annealing.
- 7. The method of claim 6, wherein the magnetization vectors are re-set to improve switching curve symmetry.

- 8. The method of claim 6, wherein the magnetization vectors are re-set to r duce critical switching field.
- 9. The method of claim 6, wherein the magnetization vectors are re-set to point in the same direction.
- 10. The method of claim 1, wherein the pinned layer magnetization vector is re-set to compensate for strong ferromagnetic coupling and weak antiferromagnetic coupling.
- 11. The method of claim 10, wherein the pinned layer magnetization vector is moved away from the sense layer magnetization vector.
- 12. The method of claim 10, wherein the pinned layer magnetization vector is re-set to improve switching curve symmetry.
- 13. The method of claim 10, wherein the pinned layer magnetization vector is re-set to reduce critical switching field.
- 14. The method of claim 1, wherein sense layer magnetization angle is changed independently of pinned layer magnetization angle.
- 15. A method comprising:
 forming a magnetic tunnel junction including pinned and sense layers;
 determining a desired switching curve for the junction; and
 re-setting a magnetization vector of at least one of the layers.
- 16. The method of claim 15, wherein both the sense layer magnetization vector and the pinned layer magnetization vector are re-set by reannealing.

- 17. The m thod of claim 16, wherein the magnetization vectors are re-set to improve switching curve symmetry.
- 18. The method of claim 16, wherein the magnetization vectors are re-set to reduce critical switching field.
- 19. The method of claim 16, wherein the magnetization vectors are re-set so that easy axes of the pinned and sense layers point in the same direction.
- 20. The method of claim 15, wherein the pinned layer magnetization vector only is re-set by re-annealing.
- 21. The method of claim 20, wherein the pinned layer magnetization vector is moved away from the sense layer magnetization vector.
- 22. The method of claim 20, wherein the pinned layer magnetization vector is re-set to improve switching curve symmetry.
- 23. The method of claim 20, wherein the pinned layer magnetization vector is re-set to reduce critical switching field.
- 24. The method of claim 20, wherein sense layer magnetization angle is changed independently of pinned layer magnetization angle.
- 25. A magnetic tunnel junction comprising:
- a pinned layer having a first magnetization vector lying in a plane of the pinned layer; and
- a sense layer having a second magnetization vector lying in a plane of the sense layer;
- at least one of the first and second magnetization vector having been reset to a different angle, the different angle corresponding to a desired switching curve of the junction.

- 26. The magnetic tunnel junction of claim 25, wherein the junction has strong ferromagnetic and antiferromagnetic coupling; and wherein both the first and second vectors have been re-set.
- 27. The magnetic tunnel junction of claim 26, wherein both vectors point in the same direction.
- 28. The magnetic tunnel junction of claim 25, wherein the junction has strong ferromagnetic coupling and weak antiferromagnetic coupling; and wherein only the first vector has been re-set.
- 29. The magnetic tunnel junction of claim 25, wherein the first vector is at a different angle than the second vector.
- 30. The magnetic tunnel junction of claim 25, wherein the magnetic tunnel junction has strong ferromagnetic coupling; and wherein at least half the switching curve is symmetric.
- 31. The magnetic tunnel junction of claim 30, wherein the magnetic tunnel junction also has strong antiferromagnetic coupling.